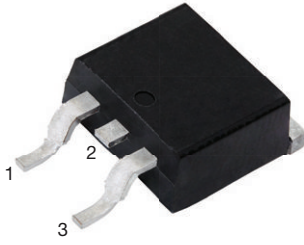
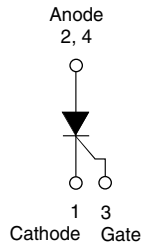


## Thyristor Surface Mount, Phase Control SCR, 8 A


**D<sup>2</sup>PAK (TO-263AB)**


### FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Designed and qualified according JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
 COMPLIANT  
 HALOGEN  
**FREE**

### APPLICATIONS

- Input rectification and crow-bar (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

### DESCRIPTION

The VS-12TTS08S-M3 High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

### PRIMARY CHARACTERISTICS

|                       |                               |
|-----------------------|-------------------------------|
| $I_{T(AV)}$           | 8 A                           |
| $V_{DRM}/V_{RRM}$     | 800 V                         |
| $V_{TM}$              | 1.2 V                         |
| $I_{GT}$              | 15 mA                         |
| $T_J$                 | -40 to +125 °C                |
| Package               | D <sup>2</sup> PAK (TO-263AB) |
| Circuit configuration | Single SCR                    |

### OUTPUT CURRENT IN TYPICAL APPLICATIONS

| APPLICATIONS   | SINGLE-PHASE BRIDGE | THREE-PHASE BRIDGE | UNITS |
|--|---------------------|--------------------|-------|
| Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W | 13.5                | 17                 | A     |

### MAJOR RATINGS AND CHARACTERISTICS

| PARAMETER         | TEST CONDITIONS     | VALUES      | UNITS |
|-------------------|---------------------|-------------|-------|
| $I_{T(AV)}$       | Sinusoidal waveform | 8           | A     |
| $I_{T(RMS)}$      |                     | 12.5        |       |
| $V_{RRM}/V_{DRM}$ |                     | 800         | V     |
| $I_{TSM}$         |                     | 110         | A     |
| $V_T$             | 8 A, $T_J = 25$ °C  | 1.2         | V     |
| $dV/dt$           |                     | 150         | V/μs  |
| $dI/dt$           |                     | 100         | A/μs  |
| $T_J$             | Range               | -40 to +125 | °C    |

### VOLTAGE RATINGS

| PART NUMBER    | $V_{RRM}$ , MAXIMUM PEAK REVERSE VOLTAGE<br>V | $V_{DRM}$ , MAXIMUM PEAK DIRECT VOLTAGE<br>V | $I_{RRM}/I_{DRM}$<br>AT 125 °C<br>mA |
|----------------|---|--|--------------------------------------|
| VS-12TTS08S-M3 | 800   | 800  | 1.0                                  |



| ABSOLUTE MAXIMUM RATINGS                            |                 |   |                                   |                   |    |
|---|-----------------|---|-----------------------------------|-------------------|----|
| PARAMETER   | SYMBOL          | TEST CONDITIONS   | VALUES                            | UNITS             |    |
| Maximum average on-state current                    | $I_{T(AV)}$     | $T_C = 108\text{ }^\circ\text{C}$ , 180° conduction, half sine wave                               | 8                                 | A                 |    |
| Maximum RMS on-state current                        | $I_{T(RMS)}$    |   | 12.5                              |                   |    |
| Maximum peak one-cycle non-repetitive surge current | $I_{TSM}$       | 10 ms sine pulse, rated $V_{RRM}$ applied, $T_J = 125\text{ }^\circ\text{C}$                      | 95                                |                   |    |
|   |                 | 10 ms sine pulse, no voltage reapplied, $T_J = 125\text{ }^\circ\text{C}$                         | 110                               |                   |    |
| Maximum $I^2t$ for fusing                           | $I^2t$          | 10 ms sine pulse, rated $V_{RRM}$ applied, $T_J = 125\text{ }^\circ\text{C}$                      | 45                                | A <sup>2</sup> s  |    |
|   |                 | 10 ms sine pulse, no voltage reapplied, $T_J = 125\text{ }^\circ\text{C}$                         | 64                                |                   |    |
| Maximum $I^2\sqrt{t}$ for fusing                    | $I^2\sqrt{t}$   | $t = 0.1\text{ ms to }10\text{ ms}$ , no voltage reapplied, $T_J = 125\text{ }^\circ\text{C}$     | 640                               | A <sup>2</sup> √s |    |
| Maximum on-state voltage drop                       | $V_{TM}$        | 8 A, $T_J = 25\text{ }^\circ\text{C}$   | 1.2                               | V                 |    |
| On-state slope resistance                           | $r_t$           | $T_J = 125\text{ }^\circ\text{C}$   | 16.2                              | mΩ                |    |
| Threshold voltage                                   | $V_{T(TO)}$     |   | 0.87                              | V                 |    |
| Maximum reverse and direct leakage current          | $I_{RM}/I_{DM}$ | $V_R = \text{Rated } V_{RRM}/V_{DRM}$   | $T_J = 25\text{ }^\circ\text{C}$  | 0.05              | mA |
|   |                 |   | $T_J = 125\text{ }^\circ\text{C}$ | 1.0               |    |
| Typical holding current                             | $I_H$           | Anode supply = 6 V, resistive load, initial $I_T = 1\text{ A}$ , $T_J = 25\text{ }^\circ\text{C}$ | 30                                |                   |    |
| Maximum latching current                            | $I_L$           | Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$                              | 50                                |                   |    |
| Maximum rate of rise of off-state voltage           | $dV/dt$         | $T_J = T_J \text{ max.}$ , linear to 80 %, $V_{DRM} = R_g - k = \text{Open}$                      | 150                               | V/μs              |    |
| Maximum rate of rise of turned-on current           | $dI/dt$         |   | 100                               | A/μs              |    |

| TRIGGERING                                  |             |   |        |       |
|---|-------------|---|--------|-------|
| PARAMETER                                   | SYMBOL      | TEST CONDITIONS   | VALUES | UNITS |
| Maximum peak gate power                     | $P_{GM}$    |   | 8.0    | W     |
| Maximum average gate power                  | $P_{G(AV)}$ |   | 2.0    |       |
| Maximum peak positive gate current          | + $I_{GM}$  |   | 1.5    | A     |
| Maximum peak negative gate voltage          | - $V_{GM}$  |   | 10     | V     |
| Maximum required DC gate current to trigger | $I_{GT}$    | Anode supply = 6 V, resistive load, $T_J = -65\text{ }^\circ\text{C}$ | 20     | mA    |
|   |             | Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$  | 15     |       |
|   |             | Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$ | 10     |       |
| Maximum required DC gate voltage to trigger | $V_{GT}$    | Anode supply = 6 V, resistive load, $T_J = -65\text{ }^\circ\text{C}$ | 1.2    | V     |
|   |             | Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$  | 1      |       |
|   |             | Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$ | 0.7    |       |
| Maximum DC gate voltage not to trigger      | $V_{GD}$    | $T_J = 125\text{ }^\circ\text{C}$ , $V_{DRM} = \text{Rated value}$    | 0.2    |       |
| Maximum DC gate current not to trigger      | $I_{GD}$    |   | 0.1    | mA    |

| SWITCHING                     |          |                                   |        |       |
|-------------------------------|----------|-----------------------------------|--------|-------|
| PARAMETER                     | SYMBOL   | TEST CONDITIONS                   | VALUES | UNITS |
| Typical turn-on time          | $t_{gt}$ | $T_J = 25\text{ }^\circ\text{C}$  | 0.8    | μs    |
| Typical reverse recovery time | $t_{rr}$ | $T_J = 125\text{ }^\circ\text{C}$ | 3      |       |
| Typical turn-off time         | $t_q$    |                                   | 100    |       |



| THERMAL AND MECHANICAL SPECIFICATIONS           |                |  |             |                        |
|---|----------------|--|-------------|------------------------|
| PARAMETER                                       | SYMBOL         | TEST CONDITIONS                          | VALUES      | UNITS                  |
| Maximum junction and storage temperature range  | $T_J, T_{Stg}$ |  | -40 to +125 | °C                     |
| Maximum thermal resistance, junction to case    | $R_{thJC}$     | DC operation                             | 1.5         | °C/W                   |
| Maximum thermal resistance, junction to ambient | $R_{thJA}$     |  | 62          |                        |
| Typical thermal resistance, case to heatsink    | $R_{thCS}$     | Mounting surface, smooth and greased     | 0.5         |                        |
| Approximate weight                              |                |  | 2           | g                      |
|   |                |  | 0.07        | oz.                    |
| Mounting torque                                 | minimum        |  | 6 (5)       | kgf · cm<br>(lbf · in) |
|   | maximum        |  | 12 (10)     |                        |
| Marking device                                  |                | Case style D <sup>2</sup> PAK (TO-263AB) | 12TTS08S    |                        |

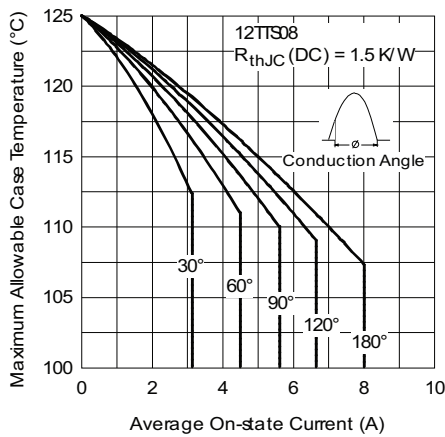


Fig. 1 - Current Rating Characteristics

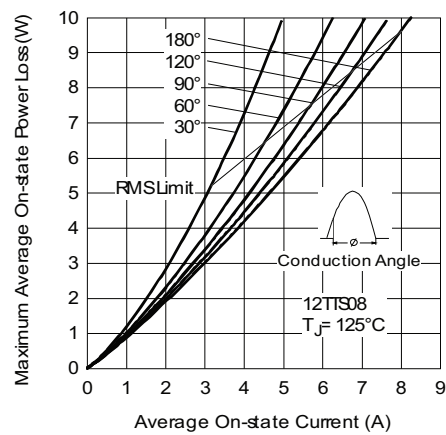


Fig. 3 - On-State Power Loss Characteristics

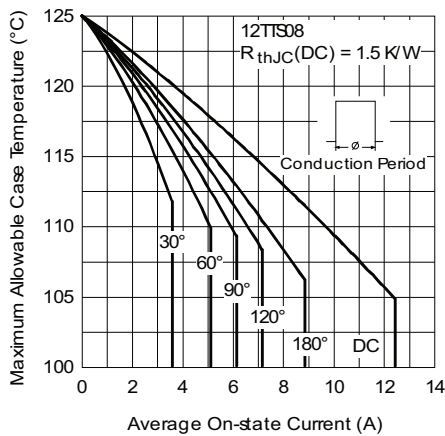


Fig. 2 - Current Rating Characteristics

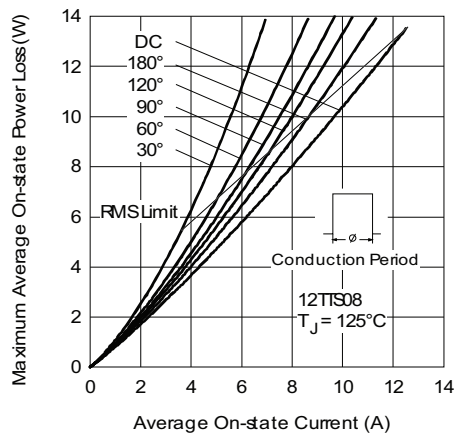


Fig. 4 - On-State Power Loss Characteristics

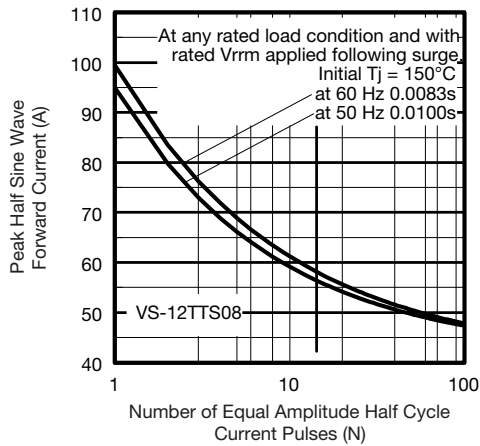


Fig. 5 - Maximum Non-Repetitive Surge Current

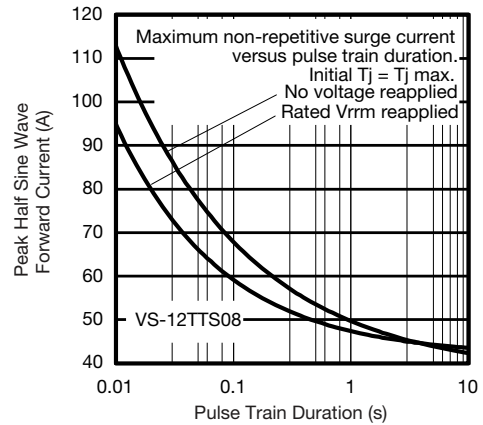


Fig. 6 - Maximum Non-Repetitive Surge Current

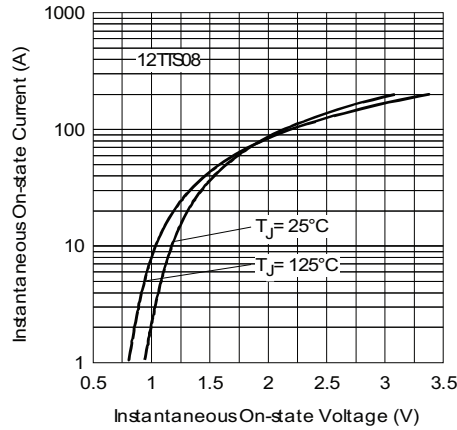


Fig. 7 - On-State Voltage Drop Characteristics

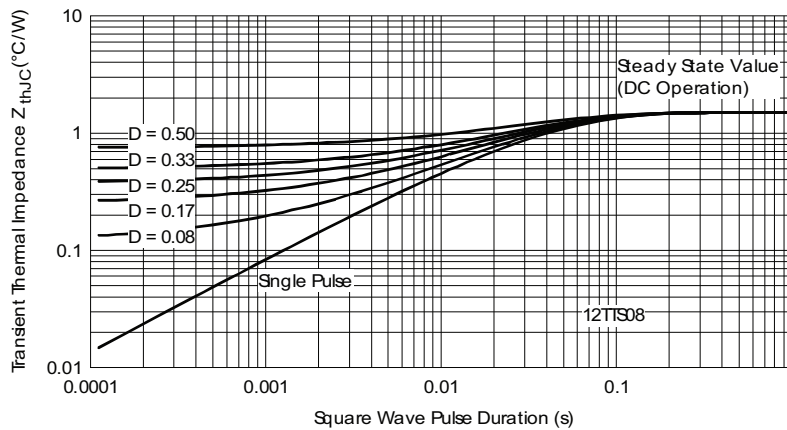
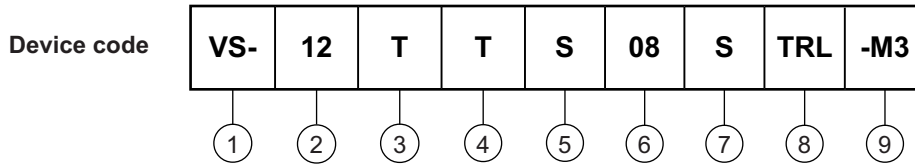


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics



## ORDERING INFORMATION TABLE



- 1** - Vishay Semiconductors product
- 2** - Current rating (12.5 A)
- 3** - Circuit configuration:  
T = single thyristor
- 4** - Package:  
T = D<sup>2</sup>PAK (TO-263AB)
- 5** - Type of silicon:  
S = standard recovery rectifier
- 6** - Voltage rating (08 = 800 V)
- 7** - S = surface mountable
- 8** -
  - None = tube
  - TRL = tape and reel (left oriented)
  - TRR = tape and reel (right oriented)
- 9** - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

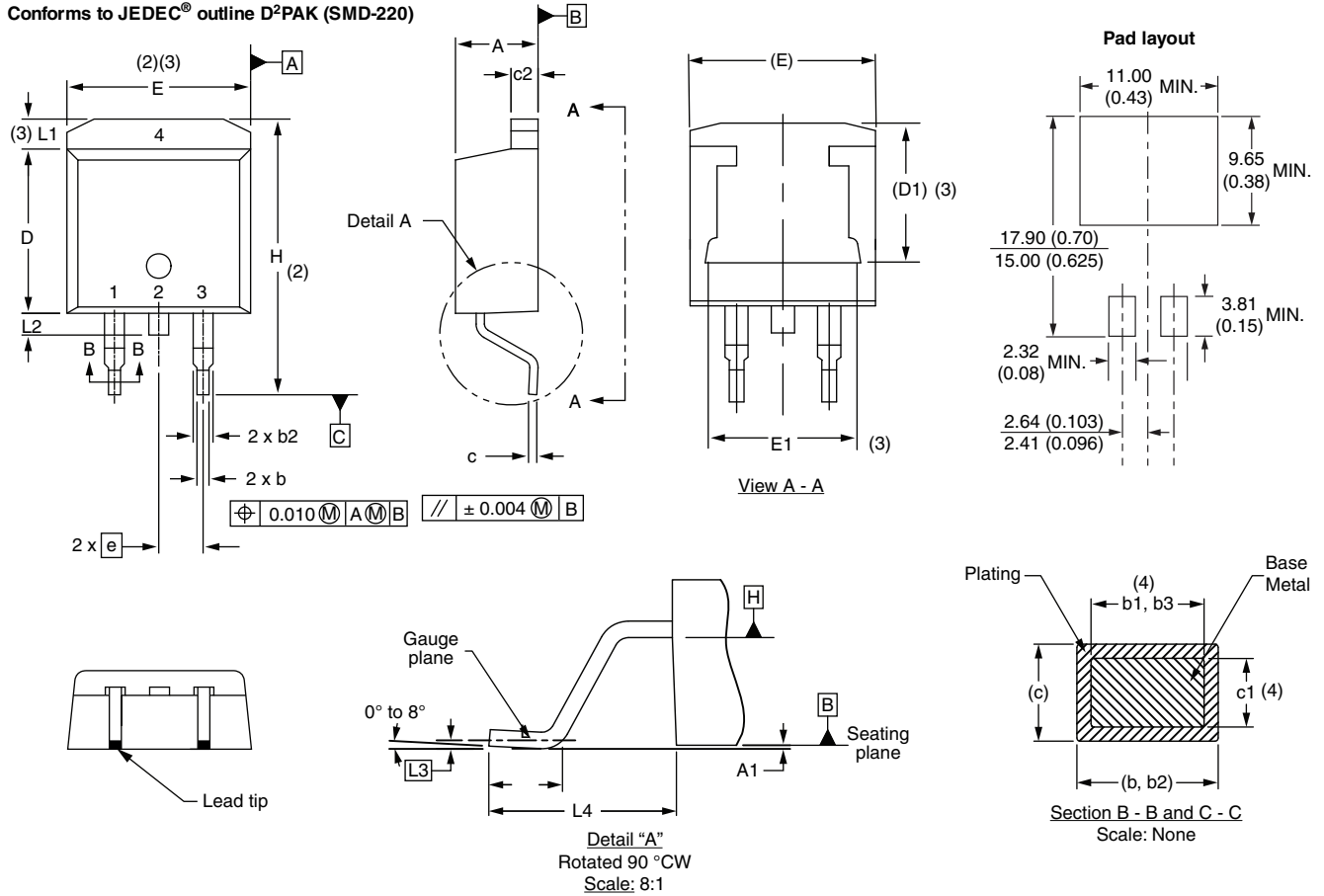
| <b>ORDERING INFORMATION</b> (Example) |                      |                                    |
|---------------------------------------|----------------------|------------------------------------|
| <b>PREFERRED P/N</b>                  | <b>BASE QUANTITY</b> | <b>PACKAGING DESCRIPTION</b>       |
| VS-12TTS08S-M3                        | 50                   | Antistatic plastic tubes           |
| VS-12TTS08STRL-M3                     | 800                  | 13" diameter plastic tape and reel |
| VS-12TTS08STRR-M3                     | 800                  | 13" diameter plastic tape and reel |

| <b>LINKS TO RELATED DOCUMENTS</b> |  |
|-----------------------------------|--|
| Dimensions                        | <a href="http://www.vishay.com/doc?96164">www.vishay.com/doc?96164</a> |
| Part marking information          | <a href="http://www.vishay.com/doc?95444">www.vishay.com/doc?95444</a> |
| Packaging information             | <a href="http://www.vishay.com/doc?96424">www.vishay.com/doc?96424</a> |

### D<sup>2</sup>PAK

#### DIMENSIONS in millimeters and inches

Conforms to JEDEC<sup>®</sup> outline D<sup>2</sup>PAK (SMD-220)



| SYMBOL | MILLIMETERS |       | INCHES |       | NOTES | SYMBOL | MILLIMETERS |       | INCHES    |       | NOTES |
|--------|-------------|-------|--------|-------|-------|--------|-------------|-------|-----------|-------|-------|
|        | MIN.        | MAX.  | MIN.   | MAX.  |       |        | MIN.        | MAX.  | MIN.      | MAX.  |       |
| A      | 4.06        | 4.83  | 0.160  | 0.190 |       | D1     | 6.86        | 8.00  | 0.270     | 0.315 | 3     |
| A1     | 0.00        | 0.254 | 0.000  | 0.010 |       | E      | 9.65        | 10.67 | 0.380     | 0.420 | 2, 3  |
| b      | 0.51        | 0.99  | 0.020  | 0.039 |       | E1     | 7.90        | 8.80  | 0.311     | 0.346 | 3     |
| b1     | 0.51        | 0.89  | 0.020  | 0.035 | 4     | e      | 2.54 BSC    |       | 0.100 BSC |       |       |
| b2     | 1.14        | 1.78  | 0.045  | 0.070 |       | H      | 14.61       | 15.88 | 0.575     | 0.625 |       |
| b3     | 1.14        | 1.73  | 0.045  | 0.068 | 4     | L      | 1.78        | 2.79  | 0.070     | 0.110 |       |
| c      | 0.38        | 0.74  | 0.015  | 0.029 |       | L1     | -           | 1.65  | -         | 0.066 | 3     |
| c1     | 0.38        | 0.58  | 0.015  | 0.023 | 4     | L2     | 1.27        | 1.78  | 0.050     | 0.070 |       |
| c2     | 1.14        | 1.65  | 0.045  | 0.065 |       | L3     | 0.25 BSC    |       | 0.010 BSC |       |       |
| D      | 8.51        | 9.65  | 0.335  | 0.380 | 2     | L4     | 4.78        | 5.28  | 0.188     | 0.208 |       |

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC<sup>®</sup> outline TO-263AB



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